

SCHOTTKY BARRIER DIODE

LBAT30LT1G
S-LBAT30LT1G

●Features

Extremely Low Forward Voltage 0.3 V (max) @ $I_F = 10 \text{ mA}$
S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

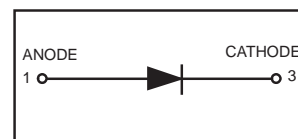
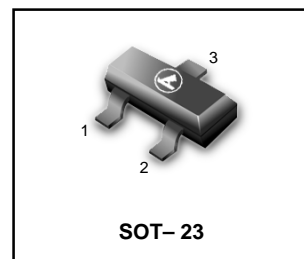
●Construction

Silicon epitaxial planar

- We declare that the material of product compliance with RoHS requirements.

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAT30LT1G S-LBAT30LT1G	T30	3000/Tape&Reel
LBAT30LT1G S-LBAT30LT1G	T30	10000/Tape&Reel



MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40~+125	$^\circ\text{C}$

*60Hz for 1cycle.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

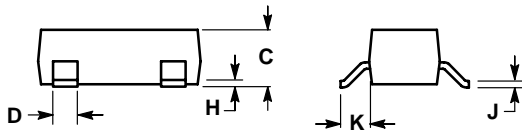
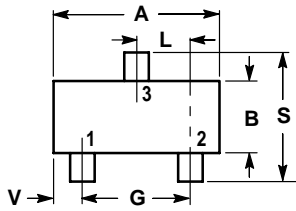
Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.30	V	$I_F = 10 \text{ mA}$
Reverse voltage	V_R	30	-	-	V	$I_R = 500 \mu\text{A}$

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SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

